Abstracts

New GaAs PIN Diodes with Lower Dissipation Loss, Faster Switching Speed at Lower Drive Power

C. Barratt, A. Christou, N. Jansen, R.E. Neidert, M.L. Ruess, Jr. and C.W. Young. "New GaAs PIN Diodes with Lower Dissipation Loss, Faster Switching Speed at Lower Drive Power." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 507-509.

GaAs PIN diode material with low forward resistance and high Q reverse bias capacitance has been successfully grown for the first time. Static performance data for shunt mounted chips in a microstrip SPST switch show improved insertion loss for the 2-40 GHz range. Dynamic data show switching speed and switch drive power advantages of GaAs over Si for both carrier injection and sweep-out modes of operation.

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